

isc N-Channel MOSFET Transistor

2SK1707

DESCRIPTION

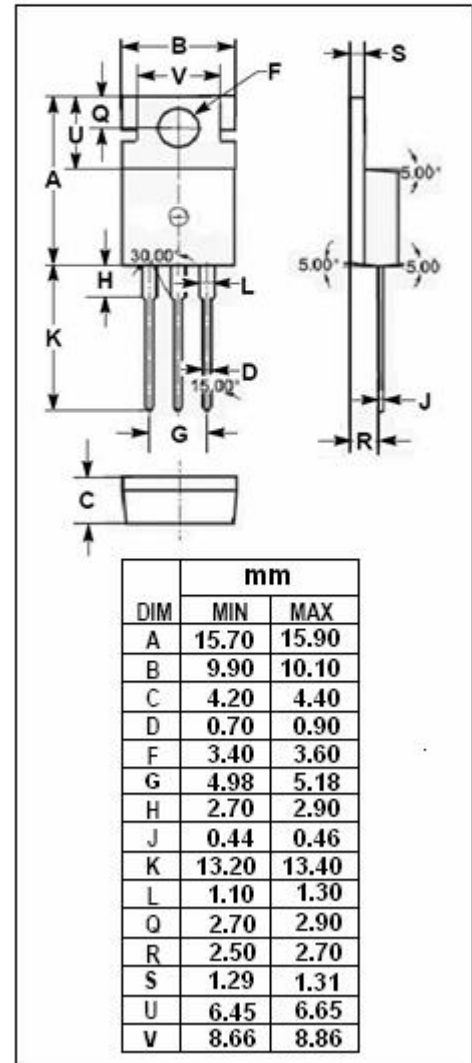
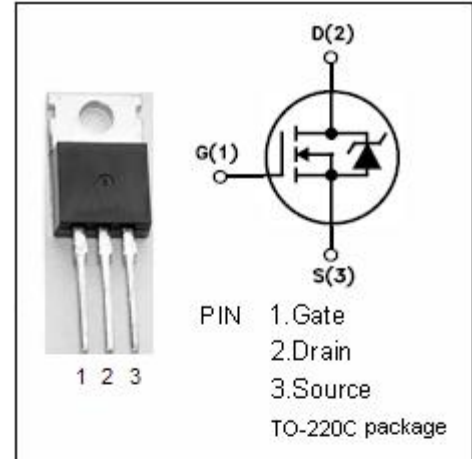
- Drain Current $-I_D = 4A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 600V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- Power supplies, converters and power motor controls

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^\circ C$	4	A
P_{tot}	Total Dissipation@ $T_C = 25^\circ C$	90	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc N-Channel MOSFET Transistor**2SK1707**• ELECTRICAL CHARACTERISTICS (T_a=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	600		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	2.0	4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 2A		2.6	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600V; V _{GS} = 0		1	mA